

MICROSCOPY OF SEMICONDUCTING MATERIALS XVI

17-20 March 2009, University of Oxford, UK

Co-Chairmen

Thomas Walther (University of Sheffield)

John Hutchison (University of Oxford)

Peter Nellist (University of Oxford)

Tony Cullis (University of Sheffield)

ORAL PROGRAMME

(ONLY PRESENTING AUTHORS ARE SHOWN ON THIS PROGRAMME. ADDITIONAL AUTHORS' DETAILS CAN BE FOUND WITHIN THE ABSTRACTS.)

Tuesday 17 March 2009

EXHIBITION OPENS

0900-1020 REGISTRATION AND COFFEE AND EXHIBITION

1025-1030 Opening Remarks
P.B. HIRSCH

SESSION A *Epitaxy I: Wide Band-Gap Nitrides* *Chair: A.J. Craven*

1030-1110 **A1** *Invited:* Observing Cluster Formation in $\text{In}_x\text{Ga}_{1-x}\text{N}$ Alloys and its Relation to Detection Limits for Single Atoms
C. KISIELOWSKI, NCEM-LBNL, Berkeley, USA

1110-1130 **A2** Electron Microscopy and 3D Atom Probe Studies of Localization Effects in InGaN Quantum Wells
C.J. HUMPHREYS, Cambridge University, UK

1130-1150 **A3** Local properties of InGaN alloys measured by temperature and excitation dependent cathodoluminescence spectral mapping
M. ALBRECHT, Leibniz-Institut für Kristallzüchtung, Germany

1150-1210 **A4** Measurement of Composition Profiles in III-Nitrides by Quantitative Scanning Transmission Electron Microscopy
A. ROSENAUER, University of Bremen, Germany

1210-1230 **A5** Structural and Electronic Properties of the GaN Surface

H. EISELE, Technische Universität Berlin, Germany

1230-1250 **A6** Epitaxial relationships between wurtzite semiconductors and R and M-plane sapphire
P. VENNEGUES, CRHEA-CNRS, Valbonne, France

1250-1400 LUNCH AND EXHIBITION

SESSION A *Epitaxy I: Wide Band-Gap Nitrides (continued)*
Chair: E. Carlino

1400-1440 **A7** *Invited:* GaN Devices Based on Nanorods
D.J. CHERNS, University of Bristol, UK

1440-1500 **A8** Triple-Twin Domains in Mg doped GaN Wurtzite Nanowires: Structural and Electronic Properties of this Zinc-Blende-like Stacking
J. ARBIOL, Universitat de Barcelona, Spain

1500-1520 **A9** Structural properties of GaN/AlN insertions in GaN nanowires grown by MBE
C. BOUGEROL, CEA-CNRS Group, Grenoble, France

1520-1540 **A10** GaN-AlGaIn-HfO based radial heterostructure nanowires
L. LARI, University of Sheffield, UK

1540-1600 **A11** Basal-plane Stacking Faults in Non-polar GaN Studied by Off-axis Electron Holography
L. LIU, University of Cambridge, UK

1600-1630 TEA AND EXHIBITION

SESSION B *Epitaxy II: Layer Characterisation*
Chair: D.J. Cherns

1630-1710 **B1** *Invited:* TEM of Growth, Structure and Phase Transitions of Epitaxial III-V Nanowires
F. GLAS, CNRS-LPN, Marcoussis, France

1710-1730 **B2** Group III-V nanowire heterostructure interface characterization using multiple transmission electron microscopy techniques
R. PENNINGTON, Technical University of Denmark, Denmark

1730-1750 **B3** Selectively growing perfect zinc blende and wurtzite InAs nanowires
J. WONG-LEUNG, Australian National University, Australia

- 1750-1810 **B4** Nitrogen-induced intermixing of InAsN quantum dots with the GaAs matrix
L. IVANOVA, Technische Universität Berlin, Germany
- 1810-1830 **B5** Analysis of the mechanism of N incorporation in N-doped GaAs quantum wells
M. HERRERA, University of CA-Davis, USA
- 1830-1915 SHERRY RECEPTION AND EXHIBITION
- 1930 DINNER
- 2030-2130 **Evening Session: Round-Table Discussion on Existence and Relevance of Clustering in InGaN Alloys (Chair: T. Walther)**

Wednesday 18 March 2009

SESSION B *Epitaxy II: Layer Characterisation (continued)* *Chair: W. Vandervorst*

- 0850-0930 **B6** *Invited*: Templated Assembly of Epitaxial Semiconductor Nanostructures
R. HULL, Rensselaer Institute, Troy, USA
- 0930-0950 **B7** Characterization of low defect density, 50 period, strain-balanced (In,Ga)As/Ga(As,P) quantum dot arrays grown by metal-organic vapor phase epitaxy on GaAs substrates
A. NORMAN, National Renewable Energy Laboratory, USA
- 0950-1010 **B8** Crystal polarity determination of heteroepitaxial GaP thin films grown on Si (001) by convergent beam
K. VOLZ, Philipps-Universität Marburg, Germany
- 1010-1040 COFFEE AND EXHIBITION

SESSION C *High Resolution Microscopy and Nanoanalysis* *Chair: M. Hecker*

- 1040-1120 **C1** *Invited*: Exploring Semiconductor Quantum Dots and Wires by High Resolution Electron Microscopy
S. MOLINA, University of Cadiz, Spain
- 1120-1140 **C2** Refinement of chemically sensitive structure factors using parallel and convergent beam electron nanodiffraction
K. MUELLER, Universität Bremen, Germany

1140-1200 **C3** Structure of an incommensurate 90° Si grain boundary resolved thanks to a probe Cs-corrector
J. ROUVIERE, CEA Grenoble, France

1200-1220 **C4** Microscopy of advanced III-V semiconductor nanostructures using laser-pulsed atom probe tomography
M. MUELLER, University of Oxford, UK

1220-1250 LUNCH

1250-1420 POSTER SESSION **PI** AND EXHIBITION

EXHIBITION CLOSES

SESSION C *High Resolution Microscopy and Nanoanalysis (continued)*
Chair: S. Molina

1420-1500 **C5** *Invited:* Quantitative Z-Contrast Atomic Resolution Studies of Semiconductor Nanostructured Materials
E. CARLINO, TASC, Trieste, Italy

1500-1520 **C6** Quantitative Z-contrast analysis of CdSe nanostructures using an aberration corrected scanning transmission electron microscope
R. KROEGER, University of York, UK

1520-1540 **C7** An “Howie and Whelan” like approach to the strain effect in HAADF
V. GRILLO, National Research Center, INFM-CNR, Italy

1540-1610 TEA

SESSION D *Quantum Domain Structures*
Chair: D. Gerthsen

1610-1650 **D1** *Invited:* Role of Al in Au-Catalysed Growth of Si Nanowires
S. KODAMBAKA, UCLA, USA

1650-1710 **D2** Detection of active dopants in silicon nanowires by electron holography
M. HERTOOG, CEA Grenoble, France

1710-1730 **D3** TEM analysis of VLS-grown CdTe/ZnTe heterostructure nanowires
H. KIRMSE, Humboldt-Universität zu Berlin, Germany

1730-1750 **D4** Doping-dependent Nanofaceting on VLS-grown Silicon Nanowire Surfaces

F. LI, University of Oxford, UK

1750-1810 **D5** Focused ion beam fabrication of nanodevices based on individual nanowires: strategy, device properties and guidelines for future work
A. ROMANO-RODRIGUEZ, University of Barcelona, Spain

1810-1830 **D6** Analysis of Kinking Nanowires by High Resolution Transmission Electron Microscopy
Y.J. HYUN, Vienna University of Technology, Austria

1930 DINNER

2030-2130 **Annual RMS Materials Lecture:**
Materials Research with the Next Generation of Electron Microscopes
J. SILCOX, Cornell University, Ithaca, USA

Thursday 19 March 2009

SESSION D *Quantum Domain Structures (continued)* *Chair: F. Glas*

0850-0930 **D7** *Invited:* On the Incorporation of Indium in InAs-Based Quantum Structures
D. GERTHSEN, University of Karlsruhe, Germany

0930-0950 **D8** Temperature dependence of coarsening in InAs on GaAs(001) quantum dots
F. ARCIPRETE, Università di Roma, Italy

0950-1010 **D9** Nanoscale phase transformations during the formation of heterojunctions in nanowires
F. ROSS, T. J. Watson Research Center, USA

1010-1030 **D10** Optical characterization of nanowire heterostructures by cathodoluminescence in a TEM
M. BREWSTER, MIT, USA

1030-1050 **D11** Investigation of the coloration of wide-bandgap semiconductors by TEM
T. REMMELE, Leibniz-Institute for Crystal Growth, Germany

1050-1120 COFFEE

SESSION E *Processed Si and Related Materials*

Chair: F. Glas

- 1120-1200 **E1** *Invited:* Nanoscale Analysis of Planar and 3D Si Structures
W. VANDERVORST, IMEC, Leuven, Belgium
- 1200-1220 **E2** Structural and optical properties of annealed SiO_x
G. NICOTRA, CNR-IMM, Catania, Italy
- 1220-1240 **E3** Structural and Compositional study of Erbium-Doped Silicon nanocrystals by HAADF, EELS and HRTEM techniques in an aberration corrected STEM
R. KASHTIBAN, University of Manchester, UK

1240-1310 LUNCH

1310-1420 POSTER SESSION **P2**

SESSION E *Processed Si and Related Materials*

Chair: C. Kisielowski

- 1420-1500 **E4** *Invited:* Prospects and Challenges for Electron Holography of Doped Semiconductors
R. DUNIN-BORKOWSKI, Technical University of Denmark, Denmark
- 1500-1520 **E5** Strain measurements in transistors by dark-field holography
F. HUE, University of Cambridge, UK
- 1520-1540 **E6** Strain analysis of Si_{1-x}Gex embedded source/drain transistors by nano-beam diffraction
P. FAVIA, IMEC, Leuven, Belgium
- 1540-1600 **E7** Advanced TEM Study of Stacked Si Nanowire Devices
M. JUBLOT, CEA, France
- 1600-1630 TEA
- 1630-1710 **E8** *Invited:* STEM-EELS Investigations of High-k Dielectrics
A.J. CRAVEN, University of Glasgow, UK
- 1710-1730 **E9** STEM EELS & EDX applications for quantitative arsenic dopant mapping in nanometer scale silicon devices
G. SERVANTON, STMicroelectronics, Crolles, France
- 1730-1750 **E10** Thermally induced structural changes of amorphous SiC

M. ISHIMARU, Osaka University, Japan

1750-1810 **E11** Ion implantation enhanced formation of 3C-SiC grains at the SiO₂/Si interface after annealing in CO gas
B. PECZ, Hungarian Academy of Sciences, Budapest, Hungary

1915-2000 WINE RECEPTION

2000 CONFERENCE DINNER

Friday 20 March 2009

SESSION F *Device Studies* *Chair: R. Hull*

0850-0930 **F1** *Invited:* Strain Analysis by NanoRaman Spectroscopy in Si Structures for CMOS Technology
M. HECKER, AMD, Dresden, Germany

0930-0950 **F2** Electron Tomography of Gate-All-Around Nanowire Transistors
P. CHERNS, CEA, Grenoble, France

0950-1010 **F3** Characterization of a FinFET 6T-SRAM cell by tomography
O. RICHARD, IMEC, Leuven, Belgium

1010-1030 **F4** 3D analysis of strain in an electrically measured strained SiGe MOSFET
S. OLSEN, Newcastle University, UK

1030-1100 COFFEE

SESSION G *Scanning Probe Applications* *Chair: R.E. Dunin-Borkowski*

1100-1140 **G1** *Invited:* Investigations of InAs QD Formation on GaAs (001) by in situ STM during MBE Growth
S. TSUKAMOTO, Anan National College of Technology, Japan

1140-1200 **G2** In situ MBE/STM study of InAs/GaAs
F. BASTIMAN, University of Sheffield, UK

1200-1220 **G3** Scanning probe microscopy studies of GaN grown by epitaxial layer overgrowth
R. OLIVER, University of Cambridge, UK

1220-1240 **G4** Observation of Dopant Profile Using Scanning Nonlinear Dielectric Microscopy
K. HONDA, Fujitsu Laboratories Ltd, Atsugi, Japan

1240-1310 LUNCH

1310-1420 POSTER SESSION **P3**

SESSION H *Advanced Scanning Ion and Electron Developments*
Chair: S. Kodambaka

1420-1500 **H1** *Invited:* The Emerging Application of He⁺ Ion Microscopy to Semiconductor Technologies
D. BELL, Harvard University, Cambridge, USA

1500-1520 **H2** Specimen preparation with focused ions, energy filters and laser beams
D. COOPER, CEA, Grenoble, France

1520-1540 **H3** Focused Ion Beam patterning to dielectrophoretically assemble single nanowire based devices
V. LA FERRARA, ENEA Research Center, Portici, Italy

1540-1600 **H4** Energy filtered scanning electron microscopy: applications to dopant contrast
C. RODENBURG, University of Sheffield, UK

1600-1620 **H5** Progress towards Quantitative Dopant Profiling in the SEM
K.W. CHEE, University of Cambridge, UK

1620-1640 **H6** Zinc blende Phase along the Arms of Wurtzite ZnO Tetrapods
L. LAZZARINI, CNR-IMEM Institute, Italy

1640-1700 **H7** The chemisorption of oxygen and its effect on the secondary electron emission of doped semiconductors
C. WALKER, University of York, UK

1700 TEA

END OF CONFERENCE
POSTER PROGRAMME

Wednesday 18 March, 1250-1420

POSTER SESSION P1 (Topics A and B)

- PI-1** Mg dopant distribution in an AlGa_N/Ga_N p-type superlattice assessed using atom probe microscopy, TEM and SIMS
Samantha Bennett, University of Cambridge, UK
- PI-2** Investigation of AlN/AlGa_N superlattices grown on high-temperature AlN layers on sapphire by metalorganic vapour phase epitaxy
Anna Mogilatenko, Humboldt Universität zu Berlin, Germany
- PI-3** Ga_N quantum dots on (Al_{0.5}Ga_{0.5})N: barriers microstructure and quantum dots morphology
Maxim Korytov, Centre National de la Recherche Scientifique, France
- PI-4** Investigation of optimum growth conditions of InAlN for application in distributed Bragg reflectors
Tom Sadler, University of Cambridge, UK
- PI-5** Microstructural characterisation of a prototype layer structure for a Ga_N-based photonic crystal cavity
EI-Ella Haitam, University of Cambridge, UK
- PI-6** Growth and structural characterization of room temperature grown Ga_N(0001)/MgAl₂O₄(111)
Vlado Lazarov, University of Oxford, UK
- PI-7** Dislocation Reduction in MOCVD grown Ga_N layers on Si(111) using Si_N_x and AlGa_N layers
Maik Haeberlen, University of Cambridge, UK
- PI-8** Simulation Supported Analysis of the Effect of Si_xN_y Monolayers in AlGa_N on the Dislocation Density Reduction
Oliver Klein, University of Ulm, Germany
- PI-9** Effects of Processing Treatments for Practically Usable and Environmentally Acceptable Catalyst Supported on S-terminated Ga_N (0001)
Nagatoshi Nishiwaki, Anan National College of Technology, Japan
- PI-10** The role of imperfect surfaces for quantitative STEM HAADF and LAADF imaging of nitride-based materials
Jon Barnard, University of Cambridge, UK
- PI-11** TEM characterization of catalyst-free and mask-free grown Ga_N nanorods
Marco Schowalter, Universität Bremen, Germany

- PI-12** Investigation of the micro-structural changes due to annealing in non-polar (11-20) GaN using transmission electron microscopy
Rui Hao, University of Cambridge, UK
- PI-13** Atomic-scale studies on the growth of Palladium and Nickel on GaN(0001)
Christiane Norenberg, Oxford University, UK
- PI-14** Lattice distortions in GaN/sapphire
Shridhara Rao, University of Cambridge, UK
- PI-15** Microstructural investigation of Al(1-x)In_xN (0.1<x<0.25) epilayers grown by metalorganic vapor phase epitaxy
Philippe Venegues, CRHEA-CNRS, France
- PI-16** Quantification of chemical composition and static atomic displacements in dilute nitride III/V compound semiconductors with (002) and (006) dark-field transmission electron microscopy
Rafael Fritz, Philipps-University Marburg, UK
- PI-17** Correlation of structural and optoelectronic properties of III/V semiconductors containing dilute amounts of Nitrogen
Kerstin Volz, Philipps-University Marburg, Germany
- PI-18** CBED investigations of silicon islands grown by epitaxial lateral overgrowth
Ines Haeusler, Humboldt-University Berlin, Germany
- PI-19** Atomic ordering in intermetallic CoAl alloys epitaxially grown on GaAs(001)
Qian Wan, Paul-Drude-Institut, Germany
- PI-20** Existence or Inexistence of Bandgap Bowing in II-VI Ternary Alloys: Comparison between Common-Anion and Common-Cation Cases
Nacir Tit, U.A.E. University, Arab Emirates

Thursday 19 March, 1310-1420

POSTER SESSION P2 (Topics C and D)

- P2-1** Nanochemistry in III-V semiconductor nanostructures revealed by laser-pulsed atom probe tomography

Michael Mueller, University of Oxford, UK

- P2-2** Nanostructural analysis of a thin-film GeMn magnetic semiconductor by atom probe tomography
David Saxey, University of Oxford, UK
- P2-3** 3D Atomic Modeling of the Hexagonal and Twinned-Cubic Phase Domains in Silicon Nanowires studied by High Resolution Transmission Electron Microscopy
Jordi Arbiol, Universitat de Barcelona, Spain
- P2-4** HRTEM Analysis of Gallium Oxide Nanostructures
Peter Pongratz, University of Vienna, Austria
- P2-5** Observation of Carrier Distribution in Compound Semiconductors using Phase-shifting Electron Holography
Hirokazu Sasaki, Furukawa Electric Co., Japan
- P2-6** Comparison of experimental and theoretical x-ray intensities from (In)GaAs specimens investigated by energy-dispersive x-ray spectroscopy
Thomas Walther, University of Sheffield, UK
- P2-7** Mean inner potentials of semiconductors calculated using density functional theory and measured from nanowires using electron holography
Robert Pennington, Technical University of Denmark, Denmark
- P2-8** Advantages of Low Beam Energies in a TEM for Valence EELS
Michael Stöger-Pollach, Vienna University of Technology, Austria
- P2-9** Frozen phonon simulation for large structures by parallel computing
Vincenzo Grillo, National Research Center INFM-CNR, Italy
- P2-10** STEM_CELL: a free software tool for (s)tem analysis and simulation
Vincenzo Grillo, National Research Center INFM-CNR, Italy
- P2-11** Through-focal HAADF-STEM of buried nanostructures
Pedro Galindo, Universidad de Cadiz, Spain
- P2-12** Preferential sites for InP/InAsP quantum wires nucleation using Molecular Dynamics
Pedro Galindo, Universidad de Cadiz, Spain
- P2-13** Z-Contrast STEM Tomography and High-Resolution Transmission Electron Microscopy analysis of Prismatic Heterostructures on the facets of Catalyst-Free GaAs Nanowires
Josep Rebled, Universitat de Barcelona, Spain

- P2-14** Characterization of Core-Shell GaAs/AlGaAs Nanowire Heterostructures using Advanced EM
Michael Tambe, MIT, USA
- P2-15** Low-voltage Scanning Transmission Electron Microscopy of InGaAs nanowires
Vincenzo Grillo, National Research Center INFM-CNR, Italy
- P2-16** Strain mapping in wurtzite InAs/InP nanowires
Francesca Rossi, IMEM-CNR Institute, Italy
- P2-17** b-SiC/SiO₂ core-shell nanowires studied by TEM and SEM-CL
Francesca Rossi, IMEM-CNR Institute, Italy
- P2-18** Insights on the growth mechanisms of ZnO nanorods by MOCVD
Pierre-Henri Jouneau, CEA-LETI, France
- P2-19** Quantitative investigation of the onset of islanding in strained layer epitaxy of InAs/GaAs
Thomas Walther, University of Sheffield, UK
- P2-20** Study of annealed InAs/GaAs quantum dot structures
Y Qiu, University of Sheffield, UK
- P2-21** Single quantum dot emission by nanoscale selective growth of InAs on GaAs: a bottom-up approach
Ernesto Placidi, Università di Roma Tor Vergata, Italy
- P2-22** TEM studies of multilayered In_{0.33}Ga_{0.67}As Quantum Dots
Shridhara Rao, University of Cambridge, UK
- P2-23** Nano-scale composition determination in III-V quantum dot systems by multi-method approach
Reza Kashtiban, University of Manchester, UK
- P2-24** Refined chemical analysis of interfaces using sigmoidal functions: application to InAs/GaSb short-period-superlattices
Esperanza Luna, Paul-Drude Institute for Solid State Electronics, Germany
- P2-25** Structure and luminescence of sol-gel synthesized anatase nanoparticles
Ute Hormann, Ulm University, Germany

Friday 20 March, 1310-1420

POSTER SESSION P3 (Topics E, F,G and H)

- P3-1** CrSi₂ thin films on silicon: texture and composition
Meiken Falke, Bruker-AXS Microanalysis, Germany
- P3-2** Characterization of ytterbium silicide formed in ultra high vacuum
Adam Łaszcz, Institute of Electron Technology, Poland
- P3-3** Chemical analysis of nickel silicides with high spatial resolution by combined EDS, EELS and ELNES
Eveline Verleysen, IMEC, Belgium
- P3-4** Evolution of Structure of Interface between Si Wafers with Hybrid Crystal Orientation in Process of High Temperature Annealing
Nikolai Zakharov, Max-Planck-Institut für Mikrostrukturphysik, Germany
- P3-5** Clathrate-I Type Borosilicides of Alkali Metals Studied by Electron Microscopy
Reiner Ramlau, Max-Planck-Institut für Chemische Physik fester Stoffe, Germany
- P3-6** Crystallographic polarity of 3C-SiC on Si(111)
Joerg Pezoldt, Institut für Mikro- und Nanotechnologien, Germany
- P3-7** The Evolution of Lattice Structure of Porous Silicon at the Storage in the Ambient Air
Lev Sorokin, Yoffe Physical-Technical Institute of the Russian Academy of Sciences, Russia
- P3-8** Ge-nanocrystals in an Al₂O₃ matrix for electronics
Reza Kashtiban, University of Manchester, UK
- P3-9** TEM analysis of novel Ge-rich SiGe MOSFET structures with high-k dielectric for high performance PMOS device technology
David Norris, University of Sheffield, UK
- P3-10** Understanding the phase images in electron holography
David Cooper, CEA, France
- P3-11** Transmission Electron Microscopy of Ferromagnetic Co-doped (La,Sr)TiO₃
Lata Sahonta, University of Cambridge, UK
- P3-12** Research of morphology and chemical compounds of structure based on Pd oxide
Sergey Zubkhov, University of Nizhni Novgorod, Russia
- P3-13** Improved strain accuracy in Nano Beam Electron Diffraction measurement

Armand Beche, CEA Grenoble, France

- P3-14** Off-axis electron holography of electrostatic potentials in transistors: interpretation of the effect of oxide charging
Filippo Ubaldi, University of Bologna, Italy
(Rafal Dunin-Borkowski to present on the day)
- P3-15** Reliability study on longer-wavelength green InGaN/GaN LED
Zonglin Li, University of Hong Kong, Hong Kong
- P3-16** in situ STM observation of ditch structures generated around InAs quantum dots on GaAs(001) grown by molecular beam epitaxy
Takashi Toujyou, Anan National College of Technology, Japan
- P3-17** Surface Investigation of Sulphur-terminated GaAs(001) Deposited with Organopalladium Catalyst
Tomoya Konishi, Anan National College of Technology, Japan
- P3-18** In situ study of GaAs Surface Structure
Faebian Bastiman, University of Sheffield, UK
- P3-19** Identification and quantification of unintentional doping in GaN by scanning capacitance microscopy
Tongtong Zhu, University of Cambridge, UK
- P3-20** High resolution Kelvin force microscopy on semiconductor materials and organic monolayers
Fiona Frehill, Agilent Technologies, UK
- P3-21** Cathodoluminescence and atomic force microscopy investigation of defects in non-polar (11-20) GaN films
Rio Chang, University of Cambridge, UK
- P3-22** Site specific dopant profiling in the scanning electron microscope
Mark Jepson, University of Sheffield, UK
- P3-23** Dopant contrast from FIB-prepared p-n junction specimens in the dual-beam SEM
KW Chee, University of Cambridge, UK
- P3-24** Quantitative HRSEM Doping Contrast via surface potential measurements using KPFM
Enrique Gruenbaum, Tel Aviv University, Israel
- P3-25** Monte Carlo Modeling of the Low-loss Electron Signal in Scanning Electron Microscopy

and Comparison with the BSE Signal
Steven Tear, University of York, UK

P3-26 Diffusion length measurement in CdHgTe with the use of EBIC
Laurent Mollard, CEA-LETI-MINATEC, France

P3-27 Photoluminescence studies of chemically deposited Cd (S-Se); CdCl₂; La films at room temperature
Smitri Agrawal, Ravishankar Shukla University, India

P3-28 Scanning Auger Microscopy for solid state nanostructures analysis
DE Nikolitchev, University of Nizhni Novgorod, Russia

Local structure analysis of Ge₂Sb₂Te₅ recording marks in the phase-change disks
Muneyuki Naito, Osaka University, Japan
(was P2-8 now withdrawn)